



2812
Attorney's Docket No.: 10559-587001
Intel Docket No.: P12768

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Been-Yih Jin, et al. Art Unit : 2812
Serial No. : 10/081,992 Examiner : Ron E. Pompey
Filed : February 21, 2002 Assignee : Intel Corporation
Title : NON-SILICON SEMICONDUCTOR AND HIGH-K GATE DIELECTRIC
METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS

Mail Stop Non-Fee Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT IN REPLY TO OFFICE ACTION OF DECEMBER 24, 2003

Please amend the above-identified application as follows:

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Date of Deposit: 2/26/04

Signature: Till Gorkman

Typed or Printed Name of Person Signing Certificate